WHAT IS CLAIMED IS:

1. An electro-optical device comprising:

a pair of substrates;

an electro-optical modulating layer provided between said substrates,

a plurality of thin film transistors provided on one of said substrates;

an electrode arrangement provided on said one of said substrates, said electrode arrangement being in the form of matrix and comprising a plurality of column lines connected to gate terminals of said thin film transistors and a plurality of row lines connected to source or drain terminals of said thin film transistors;

a first means for supplying an electric signal to said column lines, said first means being connected to said column lines; and

a second means for supplying an electric signal to said row lines, said second means being connected to said row lines,

wherein one or both of said first and second means includes other thin film transistors provided on said one of said substrates.

2. The electro-optical device of claim 1 wherein only one of said first and second means includes other thin film transistors provided on said one of said substrates and the other one of said first and second means comprises a semiconductor chip.

3. The electro-optical device of claim 1 wherein said other thin film transistors are produced by the same process as said plurality of thin film transistors.

4. The electro-optical device of claim 3 wherein the

transistors have semi-amorphous semiconductor films.

5. The electro-optical device of claim 3 wherein the transistors are insulated gate field effect transistors.

6. The electro-optical device of claim 1 wherein one of source and drain terminals, which is not connected with said row lines, of each of said plurality of thin film transistors is provided with a pixel electrode.

7. The electro-optical device of claim 1 wherein said electro-optical modulating layer comprises a liquid crystal.

8. An electro-optical device comprising:

a pair of substrates;

an electro-optical modulating layer provided between said substrates,

a plurality of complementary thin film transistors provided on one of said substrates;

an electrode arrangement provided on said one of said substrates, said electrode arrangement being in the form of matrix and comprising a plurality of column lines connected to gate terminals of said transistors and a plurality of row lines connected to source or drain terminals of said transistors;

a first means for supplying an electric signal to said column lines, said first means being connected to said column lines; and

a second means for supplying an electric signal to said row lines, said second means being connected to said row lines,

wherein at least a part of said first and second means comprises other complementary thin film transistors provided on said one of said substrates.

9. The electro-optical device of claim 8 wherein other part of said first and second means comprises a semiconductor chip.

10. The electro-optical device of claim 8 wherein the transistors have semi-amorphous semiconductor films.

11. The electro-optical device of claim 8 wherein said other complementary thin film transistors are produced by the same process as said plurality of complementary thin film transistors.

12. The electro-optical device of claim 8 wherein the transistors are insulated gate field effect transistors.

13. The electro-optical device of claim 8 wherein one of source and drain terminals, which is not connected with said row lines, of each of said plurality of complementary thin film transistors is provided with a pixel electrode.

14. The electro-optical device of claim 8 wherein said electro-optical modulating layer comprises a liquid crystal.

15. A method for manufacturing an electro-optical device comprising a pair of substrates, an electro-optical modulating layer provided between said substrates, a plurality of pixels comprising a plurality of insulated gate field effect transistors for driving said pixels, said transistors being provided on one of said substrates, and means for supplying an electric signal to said insulated gate field effect transistor, said method comprising:

forming channels of said plurality of insulated gate field effect transistors and a channel of an insulated gate field

effect transistor constituting a part of said means at the same time by forming on said one of said substrates a semiconductor film which comprises a semiconductor and extends over regions to become said channels of said plurality of insulated gate field effect transistors and a region to become said channel of an insulated gate field effect transistor constituting a part of said means and subsequently annealing said semiconductor into semi-amorphous or semi-crystal semiconductor.

16. The method of claim 15 wherein other part of said means comprises a semiconductor chip.

17. The method of claim 15 wherein said annealing is carried out in a non-oxide atmosphere.

18. The method of claim 15 wherein said semiconductor before said annealing comprises an amorphous semiconductor.

19. The method of claim 18 wherein said annealing is carried out at a temperature of 450°C to 700°C.

20. The method of claim 15 wherein said electro-optical modulating layer comprises a liquid crystal.